

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-6. (Canceled)

7. (Currently Amended) ~~The A~~ method for forming underlay coating ~~according to claim 6, for use in manufacture of semiconductor device, comprising:~~

coating an underlayer coating forming composition on a semiconductor substrate, wherein the underlayer coating forming composition comprises metal nitride particles having an average particle diameter of 1 to 1000 nm, and an organic solvent; and
baking the coated semiconductor substrate ~~wherein the baking is carried out~~
under a condition of a baking temperature of 80 to 300°C and a baking time of 0.5 to 10 minutes.

8. (Currently Amended) An underlayer coating for use in manufacture of semiconductor device, formed by
~~coating the an~~ coating an underlayer coating forming composition ~~according to claim 1 on~~
a semiconductor substrate, wherein the underlayer coating forming composition comprises metal nitride particles having an average particle diameter of 1 to 1000 nm, and an organic solvent, and
~~baking it the~~ baking the coated semiconductor substrate under a condition of a baking temperature of 80 to 300°C and a baking time of 0.5 to 10 minutes.

9-10. (Canceled)